

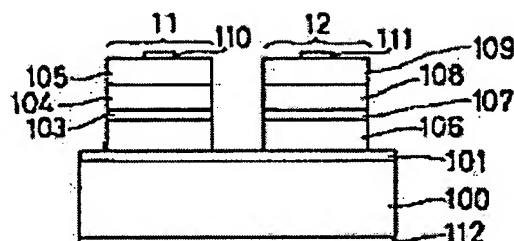
SEMICONDUCTOR LIGHT-EMITTING ELEMENT AND ITS MANUFACTURE

Patent number: JP6163988
Publication date: 1994-06-10
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Classification:
- international: H01L33/00
- european:
Application number: JP19920317416 19921126
Priority number(s):

Abstract of JP6163988

PURPOSE:To obtain a semiconductor light emitting element wherein a plurality of light emitting regions can be formed in a chip, and light emission in a wide wavelength region is realized for a far field pattern and a near field pattern.

CONSTITUTION:Semiconductor layers 11, 12 having light emission regions different in light emission wavelength region are formed on a semiconductor substrate 100. A GaAs substrate is used as the semiconductor substrate 100. The semiconductor layers are formed by using at least one kind out of Al, Ga, In, Zn and Cd, and at least one kind out of P, As, S and Se. The respective light emission regions are formed so as to have different constituent elements or composition ratios. Thereby light emission of wide wavelength region in red, green and blue wavelength regions can be realized for a far field pattern and a near field pattern.



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